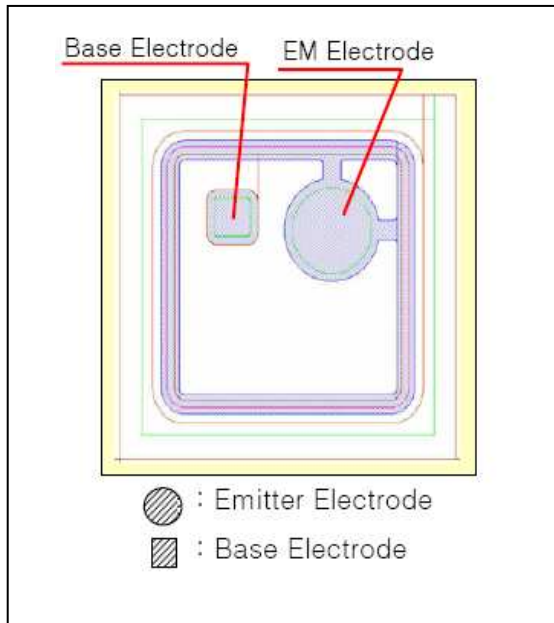


# OPB0462

## Silicon Photo Transistor

### 1. Structure

- 1.1 Chip Size : 0.46mm X 0.46mm
- 1.2 Chip thickness :  $180 \pm 15 \mu\text{m}$
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
  - Emitter : 135 $\mu\text{m}$
  - Base : 70 $\mu\text{m}$  X 70 $\mu\text{m}$



### 2. Guaranteed Probed Electrical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Leakage Current	$I_{CEO}$			50	nA	$V_{ce}=10V$
Spectrum Sensitivity	$\lambda$	500		1,050	nm	
Peak Sensing Wavelength	$\lambda_p$		880		nm	
C-E Voltage	$BV_{CEO}$	90			V	$I_{CE}=500\mu A$
C-B Voltage	$BV_{CBO}$	100			V	$I_{CB}=50\mu A$
E-B Voltage	$BV_{EBO}$	6.7			V	$I_{EB}=50\mu A$
E-C Voltage	$BV_{ECO}$	7.1			V	$I_{EC}=50\mu A$
C-E Saturation Voltage	$V_{CES}$			200	mV	$I_C=5mA, I_B=1mA$
DC Current Gain	$h_{FE}$	700		1,400	-	$V_{CE}=10V, I_c=1mA$

### 3. Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	90	V
Emitter-Collector Voltage	$V_{ECO}$	7.1	V

## AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, I

Tel. +82 63 839 1111      Fax. +82 63 835 8259

[www.auk.co.kr](http://www.auk.co.kr)

